

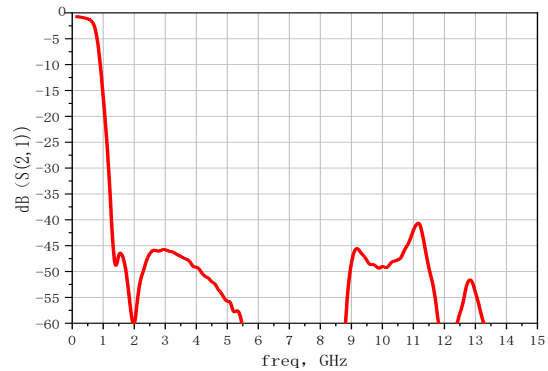
Electrical Specifications (T_A=+25°C)

| Parameter | Min. | Typ. | Max. | Unit |
|---------------------------------|-------------|------|------|------|
| Cut-off Freq. (f ₀) | - | 0.5 | - | GHz |
| Insertion Loss @ f ₀ | - | - | 1.2 | dB |
| Return Loss | 16 | - | - | dB |
| Out of band | ≥20@1.07GHz | | | dB |
| Attenuation | ≥40@1.28GHz | | | dB |

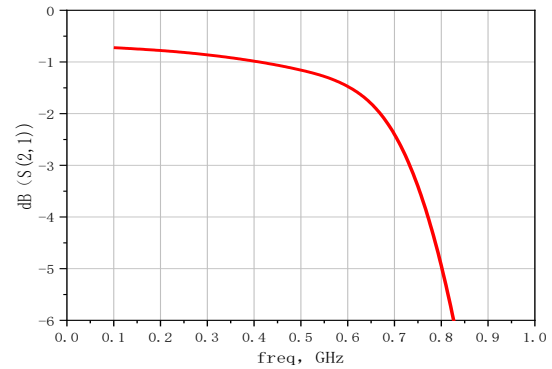
Max. Input Power 30dBm

| | |
|-----------------------|----------------|
| Operating Temperature | -55°C ~ +125°C |
| Storage Temperature | -65°C ~ +150°C |

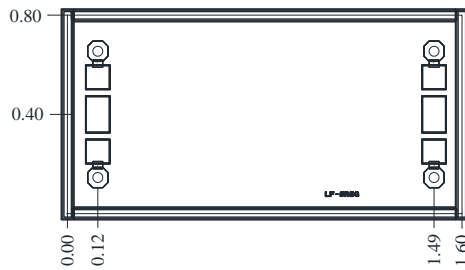
Typical widenedband Insertion Loss at T_A=25°C



Typical Insertion Loss at T_A=25°C



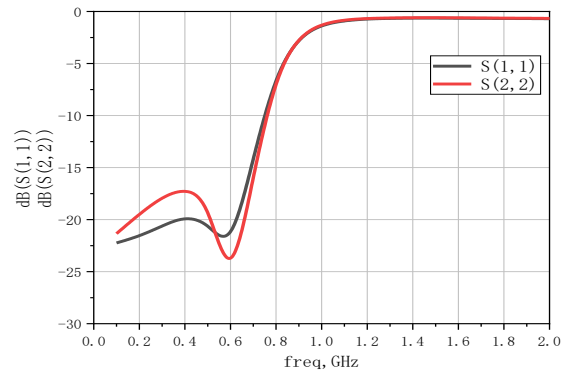
Outline Drawing



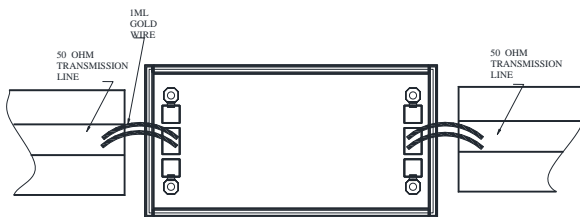
Notes:

1. Dimensions are in millimeters. Tolerance: ±0.05 mm
2. Die thickness is 0.1 mm
3. Typical bond pad size is 0.1 x 0.1 mm

Typical Return Loss at T_A=25°C



Recommended Assembly Diagram



Notes:

1. Die is back-metallized and can be mounted with AuSn eutectic preform or with electrically conductive epoxy.
2. We recommend using Φ 25um Au wire for wire-bonding, with max wire length of 400um.
3. Sinter using AuSn (80/20) alloy, ensuring the temperature does not exceed 300°C for a maximum of 30 seconds.
4. Handle die in clean environment. Do not attempt to clean the chip using liquid cleaning systems.
5. Die is ESD sensitive. ESD protection is required during usage and storage.